STATUS OF THE CLAIMS

The status of the claims of the present application stands as follows:

1. **(Currently amended)** A bipolar device, comprising:
   (a) a substrate having a collector;
   (b) an undoped epitaxial layer formed above said substrate at least above said collector;
   (c) a doped epitaxial extrinsic base layer confronting said undoped epitaxial layer and having an aperture formed therein;
   (d) an emitter ~~spaced from said collector~~having a lower portion located in said aperture and confronting said undoped epitaxial layer; and
   (ee) ~~a base having a first portion located between said substrate and said emitter and a second portion surrounding said first portion, said base including a first conductor located within said first and second portions and having a first conductance in said first portion and a second conductance in said second portion, wherein said first conductance and said second conductance are substantially the same as one another~~ a conductor ring formed in said doped epitaxial extrinsic based layer surrounding said lower portion of said base.

2. **(Currently amended)** A bipolar device according to claim 1, ~~wherein said base comprises at least one epitaxial semiconductor layer~~further comprising a doped epitaxial intrinsic base layer located between said undoped epitaxial layer and said substrate.

3. **(Currently amended)** A bipolar device according to claim 1, wherein said emitter includes an upper portion distal from said substrate ~~and a lower portion located between said upper portion and said collector, said second portion of said base being located between said upper portion of said emitter and said substrate~~ and extending over a portion of said doped epitaxial extrinsic base layer, said conductor ring extending radially out from underneath said upper portion.

4. **(Currently amended)** A bipolar device according to claim 1, wherein said ~~first~~ conductor ring comprises a ~~silicide~~silicidated region of said doped epitaxial extrinsic base layer.

5. **(Currently amended)** A bipolar device according to claim 1, ~~further comprising a second conductor contained only in said second portion of said base~~wherein said doped epitaxial extrinsic base layer has a thickness and said conductor ring has a thickness less than the thickness of said doped epitaxial extrinsic base layer.

6. **(Currently amended)** A bipolar device according to claim ~~5~~1, wherein ~~each of said first and second conductors comprises a silicide~~said doped epitaxial extrinsic base layer includes a remnant oxidated ring immediately surrounding said lower portion of said emitter.

7. **(Currently amended)** A bipolar device, comprising:

(a) a substrate having a collector formed therein;

(b) a doped epitaxial intrinsic base layer formed on said substrate;

(c) an undoped epitaxial layer formed on said doped epitaxial intrinsic base layer;

(d) a doped epitaxial extrinsic base layer formed on said undoped epitaxial layer and including an aperture;

(e) an emitter including a lower portion ~~located proximate said collector~~ and an upper portion ~~located distal said collector and extending beyond said lower portion so as to form an overlap region with respect to said substrate~~, said lower portion being located in said aperture and said upper portion being located above said lower portion and extending over a portion of said doped epitaxial extrinsic base layer; and

(e~~f~~) a ~~base disposed on said substrate between said collector and said emitter and including a first~~ conductor ~~extending both inside and outside said overlap region and having a substantially uniform conductance~~formed in said doped epitaxial extrinsic base layer and located both underneath a portion of said upper portion of said emitter and out from underneath said upper portion of said emitter.

8. **(Currently amended)** A bipolar device according to claim 7, wherein said ~~base comprises at least one epitaxial semiconductor layer~~doped epitaxial extrinsic base layer includes a remnant oxidated ring immediately surrounding said lower portion of said emitter.

9. **(Currently amended)** A bipolar device according to claim 7, wherein said ~~first~~ conductor comprises a ~~silicide~~silicidated region of said doped epitaxial layer.

10. **(Currently amended)** A bipolar device according to claim 7, further comprising a ~~second conductor contained only in said second portion of said base~~ landing pad remnant located on said doped epitaxial extrinsic base layer surrounding said aperture.

11. **(Currently amended)** A bipolar device according to claim 10, ~~wherein each of said first and second conductors comprises a silicide~~further comprising a nitride spacer located on top of said landing pad remnant.

12. **(Withdrawn)** A method of forming a bipolar device on a substrate having a collector, comprising the steps of:
    (a) forming an intrinsic base layer on said substrate;
    (b) forming a first conductor above said intrinsic base layer, wherein said first conductor has a substantially uniform conductance throughout; and
    (c) forming an emitter having at least a portion thereof extending over a portion of said first conductor.

13. **(Withdrawn)** A method according to claim 12, wherein step a includes forming an intentionally undoped layer.

14. **(Withdrawn)** A method according to claim 12, wherein step b includes forming a first extrinsic base layer and silicidating said first extrinsic base layer prior to step c so as to form said first conductor.

15. **(Withdrawn)** A method according to claim 14, wherein step b further includes forming a landing pad atop said first extrinsic base layer prior to silicidating said first extrinsic base layer.

16. **(Withdrawn)** A method according to claim 15, wherein step c includes removing a portion of said landing pad to form an aperture.

17. **(Withdrawn)** A method according to claim 16, wherein step c further includes oxidizing said first extrinsic base layer beneath said aperture so as to form an oxidized region and removing at least a portion of said oxidized region to said intrinsic base layer.

18. **(Withdrawn)** A method according to claim 14, further comprising the step of forming a second extrinsic base layer above said first extrinsic base layer and performing a first etch through said second extrinsic base layer to said first extrinsic base layer and then performing a second etch through said first extrinsic base layer to said intrinsic base layer.

19. **(Withdrawn)** A method according to claim 12, further comprising the step of forming a second conductor that does not extend underneath said emitter.

20. **(Withdrawn)** A method according to claim 19, wherein said second conductor is formed by silicidation.

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